SPTECH Silicon NPN Power Transistor

DESCRIPTION

High Switching Speed

• High Voltage

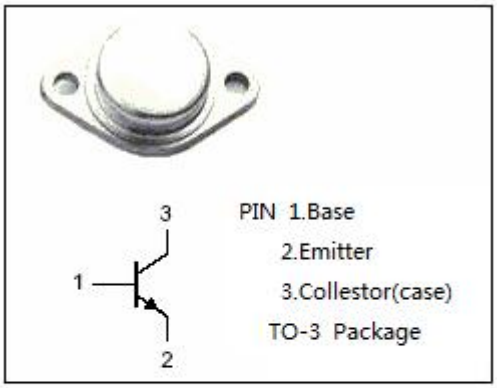
APPLICATIONS

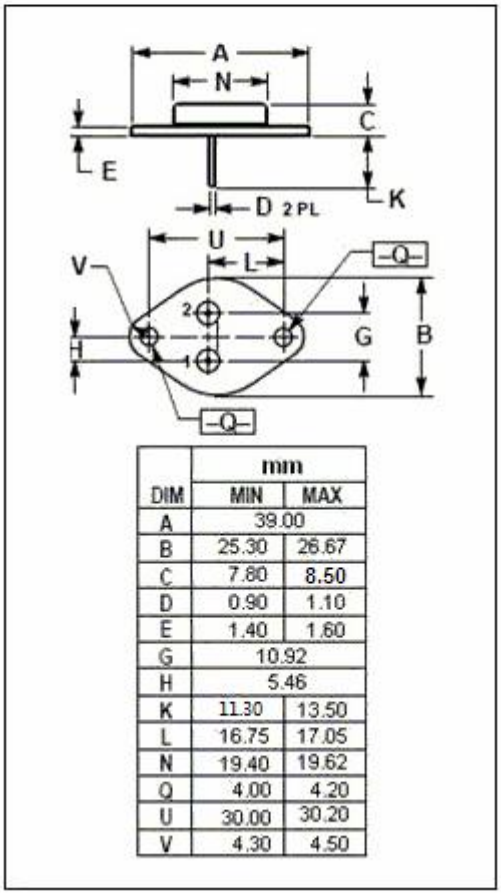
• Converters

• Inverters

• Switching regulators

• Motor controls





DIM	mm MIN	MAX
A	39.00	
B	25.30	26.67
C	7.80	8.50
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.30	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	MAX	UNIT
V_{CBO}	Collector-Base Voltage	1000	V
V_{CEO}	Collector-Emitter Voltage	450	V
V_{EBO}	Emitter-Base Voltage	9	V
I_C	Collector Current-Continuous	15	A
I_{CM}	Collector Current-Peak	30	A
I_B	Base Current	6	A
I_{BM}	Base Current-Peak	9	A
P_C	Collector Power Dissipation @T_C=25℃	175	W
T_j	Junction Temperature	200	℃
T_{stg}	Storage Temperature Range	-65~200	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance, Junction to Case	1.0	℃/W

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C=50mA ; I_B= 0	450			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 8A; I_B= 1.6A			1.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 8A; I_B= 1.6A			1.6	V
I_{CES}	Collector Cutoff Current	V_{CE}=$V_{CESMmax}$; V_{BE}= 0 V_{CE}= $V_{CESMmax}$;V_{BE}= 0;T_C= 125℃			1 4	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 9V; I_C= 0			10	mA
h_{FE}	DC Current Gain	I_C= 2A ; V_{CE}= 5V	15		50	

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